

# Pedram Razavi

## List of Publications by Year in descending order

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32  
papers

4,010  
citations

471509

17  
h-index

552781

26  
g-index

32  
all docs

32  
docs citations

32  
times ranked

1831  
citing authors

#	ARTICLE	IF	CITATIONS
1	Nanowire transistors without junctions. Nature Nanotechnology, 2010, 5, 225-229.	31.5	1,993
2	Performance estimation of junctionless multigate transistors. Solid-State Electronics, 2010, 54, 97-103.	1.4	487
3	High-Temperature Performance of Silicon Junctionless MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 620-625.	3.0	359
4	Reduced electric field in junctionless transistors. Applied Physics Letters, 2010, 96, 073510.	3.3	269
5	Junctionless Multiple-Gate Transistors for Analog Applications. IEEE Transactions on Electron Devices, 2011, 58, 2511-2519.	3.0	234
6	Low subthreshold slope in junctionless multigate transistors. Applied Physics Letters, 2010, 96, .	3.3	195
7	Mobility enhancement effect in heavily doped junctionless nanowire silicon-on-insulator metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2012, 101, 213502.	3.3	45
8	Improvement of carrier ballisticity in junctionless nanowire transistors. Applied Physics Letters, 2011, 98, .	3.3	43
9	Bipolar effects in unipolar junctionless transistors. Applied Physics Letters, 2012, 101, 093507.	3.3	39
10	Mobility improvement in nanowire junctionless transistors by uniaxial strain. Applied Physics Letters, 2010, 97, .	3.3	38
11	Junctionless Nanowire Transistor: Complementary Metal-Oxide-Semiconductor Without Junctions. Science of Advanced Materials, 2011, 3, 477-482.	0.7	36
12	A new F(ast)-CMS NEGF algorithm for efficient 3D simulations of switching characteristics enhancement in constricted tunnel barrier silicon nanowire MuGFETs. Journal of Computational Electronics, 2009, 8, 287-306.	2.5	31
13	Device Design and Estimated Performance for p-Type Junctionless Transistors on Bulk Germanium Substrates. IEEE Transactions on Electron Devices, 2012, 59, 2308-2313.	3.0	31
14	A Simulation Comparison between Junctionless and Inversion-Mode MuGFETs. ECS Transactions, 2011, 35, 63-72.	0.5	29
15	Influence of channel material properties on performance of nanowire transistors. Journal of Applied Physics, 2012, 111, .	2.5	24
16	Electrical performance of III-V gate-all-around nanowire transistors. Applied Physics Letters, 2013, 103, .	3.3	22
17	Effect of intravalley acoustic phonon scattering on quantum transport in multigate silicon nanowire metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2010, 108, 034510.	2.5	19
18	Nanowire zero-capacitor DRAM transistors with and without junctions. , 2010, , .		17

#	ARTICLE	IF	CITATIONS
19	Emission and absorption of optical phonons in Multigate Silicon Nanowire MOSFETs. Journal of Computational Electronics, 2012, 11, 249-265.	2.5	16
20	Simulation of Quantum Current Oscillations in Trigate SOI MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 1102-1109.	3.0	15
21	Influence of discrete dopant on quantum transport in silicon nanowire transistors. Solid-State Electronics, 2012, 70, 92-100.	1.4	15
22	Random dopant variation in junctionless nanowire transistors. , 2011, , .		9
23	Nanowire to Single-Electron Transistor Transition in Trigate SOI MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 26-32.	3.0	9
24	Influence of Elastic and Inelastic Electron-Phonon Interaction on Quantum Transport in Multigate Silicon Nanowire MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 1029-1037.	3.0	9
25	Characterization of a junctionless diode. Applied Physics Letters, 2011, 99, 013502.	3.3	6
26	Intrinsic gate delay and energy-delay product in junctionless nanowire transistors. , 2012, , .		6
27	Effect of strain and diameter on electronic and charge transport properties of indium arsenide nanowires. Solid-State Electronics, 2018, 149, 6-14.	1.4	6
28	Dissipative transport in Multigate silicon nanowire transistors. , 2010, , .		4
29	Influence of surface stoichiometry and quantum confinement on the electronic structure of small diameter In <sub>x</sub> Ga <sub>1-x</sub> As nanowires. Materials Chemistry and Physics, 2018, 206, 35-39.	4.0	2
30	Influence of Surface Passivation on Indium Arsenide Nanowire Band Gap Energies. Journal of Electronic Materials, 2019, 48, 6654-6660.	2.2	2
31	Sensitivity analysis of steep subthreshold slope (S-slope) in Junctionless nanotransistors. , 2012, , .		0
32	Electron transport in germanium junctionless nanowire transistors. , 2012, , .		0